

FORM PTO-1449 (Modified) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		Attorney Docket No. AM1771-4/T19930	Serial No.: Unassigned 08/988,246
		Applicant: SÉBASTIEN RAOUX, et al.	
		Filing Date: Herewith	Group: Unassigned

JC561 U.S. PTO
 08/988246
 12/01/97

Reference Designation		U.S. PATENT DOCUMENTS				
Examiner Initial	Document No.	Date	Name	Class	Sub-class	Filing Date (If Appropriate)
AA <i>RZ</i>	4,854,263	08/08/89	Chang et al.	118	715	08/14/87
AB <i>RZ</i>	08/748,094	---	Yieh, et al.	---	---	11/13/96
AC <i>RZ</i>	08/800,096	---	Zhao, et al.	---	---	02/12/97

FOREIGN PATENT DOCUMENTS						
	Document No.	Date	Country	Class	Sub-class	Translation (yes/no)

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)	
AD <i>RZ</i>	D.G. Hemmes et al., "Control of Stress, Stability, and Mechanical Properties of PECVD Dielectric Films for GaAs and Si Applications," <i>ECS 9th Symposium on Plasma Processing #131</i> , pgs. 1-8.
AE <i>RZ</i>	A. Tsukune et al., "Properties of Silicon Nitride Films Prepared by Dual RF Plasma Deposition," <i>Fujitsu Limited, Abstract No. 385</i> , pg. 580.
AF <i>RZ</i>	E. van de Ven et al., "Advantages of Dual Frequency PECVD for Deposition of ILD and Passivation Films," <i>7th International IEEE VLSI Multilevel Interconnection Conference, June 12-13, 1990, Santa Clara, CA</i> , (June 1990).
AG <i>RZ</i>	M. Lieberman et al., "Principles of Plasma Discharges and Materials Processing," <i>John Wiley & Sons, Inc.</i> , pgs. 328-339, (1994).

EXAMINER <i>Andy Gougin</i>	DATE CONSIDERED <i>3/18/99</i>
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.